

MOSEL VITELIC**V53C318160A****3.3 VOLT 1M X 16 FAST PAGE MODE
CMOS DYNAMIC RAM**

HIGH PERFORMANCE	50	60	70
Max. $\overline{\text{RAS}}$ Access Time, (t_{RAC})	50 ns	60 ns	70 ns
Max. Column Address Access Time, (t_{CAA})	25 ns	30 ns	35 ns
Min. Fast Page Mode Cycle Time, (t_{PC})	35 ns	40 ns	45 ns
Min. Read/Write Cycle Time, (t_{RC})	90 ns	104 ns	124 ns

Features

- 1M x 16-bit organization
- Fast Page Mode for a sustained data rate of 29 MHz
- $\overline{\text{RAS}}$ access time: 50, 60, 70 ns
- Dual $\overline{\text{CAS}}$ Inputs
- Low power dissipation
- Read-Modify-Write, $\overline{\text{RAS}}$ -Only Refresh, $\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$ Refresh, Hidden Refresh, and Self Refresh.
- Refresh Interval: 1024 cycles/16 ms
1024 cycles/256 ms (L-version)
- Available in 42-pin 400 mil SOJ and 50/44-pin 400 mil TSOP-II
- Single +3.3 V ± 0.3 V Power Supply
- LVTTTL Interface

Description

The V53C318160A is a 1048576 x 16 bit high-performance CMOS dynamic random access memory. The V53C318160A offers Fast Page mode operation. The V53C318160A has an symmetric address, 10-bit row and 10-bit column.

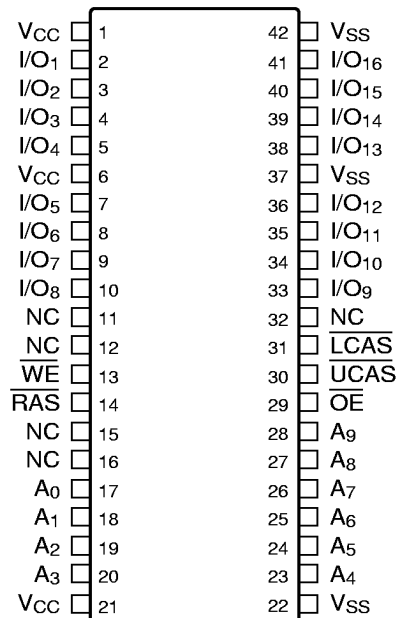
All inputs are LVTTTL compatible. Fast Page Mode operation allows random access up to 1024 x 16 bits, within a page, with cycle times as short as 35 ns.

These features make the V53C318160A ideally suited for a wide variety of high performance computer systems and peripheral applications.

Device Usage Chart

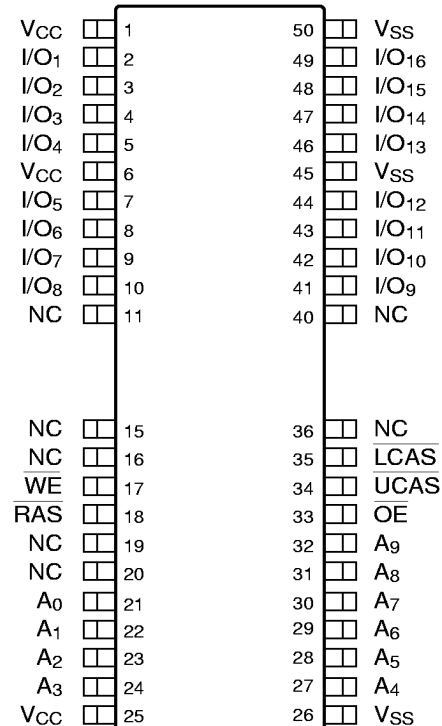
Operating Temperature Range	Package Outline		Access Time (ns)			Power		Temperature Mark
	K	T	50	60	70	Std.	L	
0°C to 70°C	•	•	•	•	•	•	•	Blank

42-Pin Plastic SOJ
PIN CONFIGURATION
Top View



311816500-02

50/44-Pin Plastic TSOP-II
PIN CONFIGURATION
Top View



311816500-03

Pin Names

A ₀ –A ₉	Row, Column Address Inputs
$\overline{\text{RAS}}$	Row Address Strobe
$\overline{\text{UCAS}}$	Column Address Strobe/Upper Byte Control
$\overline{\text{LCAS}}$	Column Address Strobe/Lower Byte Control
$\overline{\text{WE}}$	Write Enable
$\overline{\text{OE}}$	Output Enable
I/O ₁ –I/O ₁₆	Data Input, Output
V _{CC}	+3.3V Supply
V _{SS}	0V Supply
NC	No Connect

Description	Pkg.	Pin Count
SOJ	K	42
TSOP-II	T	50

Absolute Maximum Ratings*

Operating temperature range 0 to 70 °C
 Storage temperature range -55 to 150 °C
 Soldering temperature 260 °C
 Soldering time 10 s
 Input/output voltage -0.5 to min ($V_{CC}+0.5$, 4.6) V
 Power supply voltage -0.5V to 4.6 V
 Power dissipation 1.0 W
 Data out current (short circuit) 50 mA

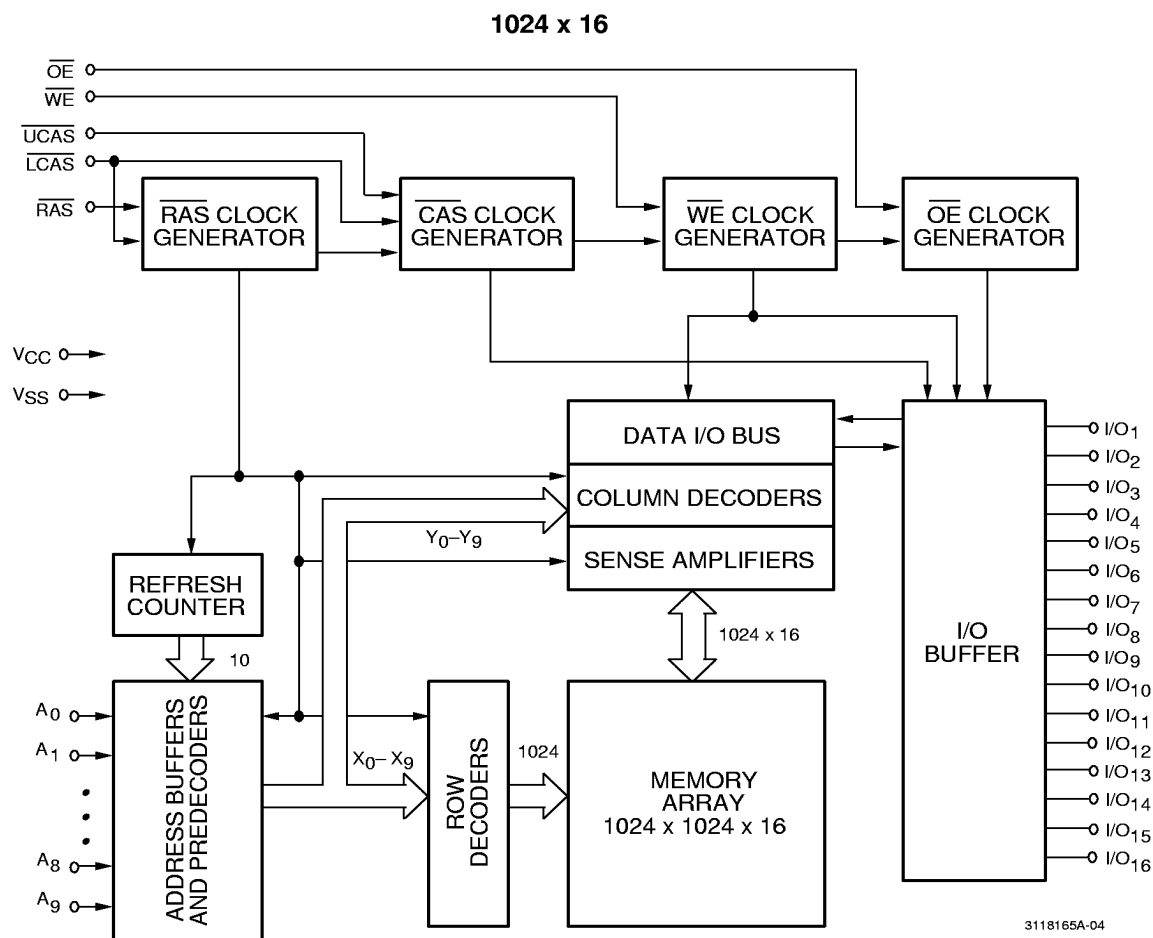
***Note:** Operation above Absolute Maximum Ratings can adversely affect device reliability.

Capacitance*

$T_A = 25^\circ\text{C}$, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $V_{SS} = 0 \text{ V}$, $f = 1 \text{ MHz}$

Symbol	Parameter	Min.	Max.	Unit
C_{IN1}	Address Input	—	5	pF
C_{IN2}	$\overline{\text{RAS}}$, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$	—	7	pF
C_{OUT}	Data Input/Output	—	7	pF

***Note:** Capacitance is sampled and not 100% tested.

Block Diagram

DC and Operating Characteristics (1-2)

$T_A = 0^{\circ}\text{C}$ to 70°C , $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $V_{SS} = 0\text{ V}$, $t_T = 2\text{ ns}$, unless otherwise specified.

Symbol	Parameter	Access Time	V53C318160A			Unit	Test Conditions	Notes
			Min.	Typ.	Max.			
I_{LI}	Input Leakage Current (any input pin)		-10		10	μA	$V_{SS} \leq V_{IN} \leq V_{CC} + 0.3\text{ V}$	1
I_{LO}	Output Leakage Current (for High-Z State)		-10		10	μA	$V_{SS} \leq V_{OUT} \leq V_{CC} + 0.3\text{ V}$ $\overline{\text{RAS}}, \overline{\text{CAS}}$ at V_{IH}	1
I_{CC1}	V_{CC} Supply Current, Operating	50			200	mA	$t_{RC} = t_{RC}(\text{min.})$	2, 3, 4
		60			180			
		70			160			
I_{CC2}	V_{CC} Supply Current, TTL Standby				2	mA	$\overline{\text{RAS}}, \overline{\text{CAS}}$ at V_{IH} other inputs $\geq V_{SS}$	
I_{CC3}	V_{CC} Supply Current, $\overline{\text{RAS}}$ -Only Refresh	50			200	mA	$t_{RC} = t_{RC}(\text{min.})$	2, 4
		60			180			
		70			160			
I_{CC4}	V_{CC} Supply Current, Fast Page Mode Operation	50			55	mA	Minimum Cycle	2, 3, 4
		60			50			
		70			45			
I_{CC5}	V_{CC} Supply Current, CMOS Standby				1.0	mA	$\overline{\text{RAS}} \geq V_{CC} - 0.2\text{ V}$, $\overline{\text{CAS}} \geq V_{CC} - 0.2\text{ V}$	1
I_{CC6}	Average Self Refresh Current CBR cycle with $t_{RAS} > t_{RASS} \text{ min.}$, $\overline{\text{CAS}}$ held low, $\overline{\text{WE}} = V_{CC} - 0.2\text{ V}$, Address and $D_{IN} = V_{CC} - 0.2\text{ V}$ or 0.2 V				1.0 250	mA μA	L version	
I_{CC7}	V_{CC} Supply Current, during $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Refresh	50			200	mA	$t_{RC} = t_{RC}(\text{min})$	2, 4
		60			180			
		70			160			
V_{IL}	Input Low Voltage		-0.5		0.8	V		1
V_{IH}	Input High Voltage		2		$V_{CC} + 0.5$	V		1
V_{OL}	Output Low Voltage				0.4	V	$I_{OL} = 2\text{ mA}$	1
V_{OH}	Output High Voltage		2.4			V	$I_{OH} = -2\text{ mA}$	1

AC Characteristics

$T_A = 0^\circ\text{C}$ to 70°C , $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $V_{SS} = 0\text{V}$, $t_T = 2\text{ns}$ unless otherwise noted

#	JEDEC Symbol	Symbol	Parameter	50		60		70		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.		
1	t_{RL1RH1}	t_{RAS}	$\overline{RAS}$ Pulse Width	50	10K	60	10K	70	10K	ns	
2	t_{RL2RL2}	t_{RC}	Read or Write Cycle Time	90		110		130		ns	
3	t_{RH2RL2}	t_{RP}	$\overline{RAS}$ Precharge Time	30		40		50		ns	
4	t_{RL1CH1}	t_{CSH}	$\overline{CAS}$ Hold Time	50		60		70		ns	
5	t_{CL1CH1}	t_{CAS}	$\overline{CAS}$ Pulse Width	13	10K	15	10K	20	10K	ns	
6	t_{RL1CL1}	t_{RCD}	$\overline{RAS}$ to $\overline{CAS}$ Delay	18	37	20	45	20	50	ns	
7	t_{WH2CL2}	t_{RCS}	Read Command Setup Time	0		0		0		ns	
8	t_{AVRL2}	t_{ASR}	Row Address Setup Time	0		0		0		ns	
9	t_{RL1AX}	t_{RAH}	Row Address Hold Time	8		10		10		ns	
10	t_{AVCL2}	t_{ASC}	Column Address Setup Time	0		0		0		ns	
11	t_{CL1AX}	t_{CAH}	Column Address Hold Time	10		15		15		ns	
12	$t_{CL1RH1(R)}$	t_{RSH}	$\overline{RAS}$ Hold Time	13		15		20		ns	
13	t_{CH2RL2}	t_{CRP}	$\overline{CAS}$ to $\overline{RAS}$ Precharge Time	5		5		5		ns	
14	t_{CH2WX}	t_{RCH}	Read Command Hold Time Referenced to $\overline{CAS}$	0		0		0		ns	9
15	t_{RH2WX}	t_{RRH}	Read Command Hold Time Referenced to $\overline{RAS}$	0		0		0		ns	9
16	t_{CL1}	t_{COH}	Output Hold after $\overline{CAS}$ LOW	5		5		5		ns	
17	t_{GL1QV}	t_{OAC}	Access Time from $\overline{OE}$		13		15		20	ns	
18	t_{CL1QV}	t_{CAC}	Access Time from $\overline{CAS}$		13		15		20	ns	7, 12
19	t_{RL1QV}	t_{RAC}	Access Time from $\overline{RAS}$		50		60		70	ns	7, 12
20	t_{AVQV}	t_{CAA}	Access Time from Column Address		25		30		35	ns	7, 13
21	t_{CL1QX}	t_{CLZ}	$\overline{CAS}$ to Low-Z Output	0		0		0		ns	7
22	t_{CH2QX}	t_{OFF}	Output Buffer Turnoff Delay	0	13	0	15	0	20	ns	
23	t_{CL1QZ}	t_{DZC}	Data to $\overline{CAS}$ Low Delay	0		0		0		ns	15
24	t_{RL1AV}	t_{RAD}	$\overline{RAS}$ to Column Address Delay Time	13	25	15	30	15	35	ns	
25	t_{GL2QZ}	t_{OEZ}	Output Buffer Turnoff Delay from $\overline{OE}$	0	13	0	15	0	17	ns	8
26	t_{WL1CH1}	t_{CWL}	Write Command to $\overline{CAS}$ Lead Time	13		15		20		ns	
27	t_{WL1CL2}	t_{WCS}	Write Command Setup Time	0		0		0		ns	11
28	t_{CL1WH1}	t_{WCH}	Write Command Hold Time	8		10		10		ns	
29	t_{WL1WH1}	t_{WP}	Write Pulse Width	8		10		10		ns	
30	t_{GL1QZ}	t_{DEQ}	Data to $\overline{OE}$ Delay	0		0		0		ns	15
31	t_{WL1RH1}	t_{RWL}	Write Command to $\overline{RAS}$ Lead Time	13		15		17		ns	
32	t_{DVWL2}	t_{DS}	Data in Setup Time	0		0		0		ns	10

AC Characteristics (Cont'd)

#	JEDEC Symbol	Symbol	Parameter	50		60		70		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.		
33	t _{WL1DX}	t _{DH}	Data in Hold Time	10		10		15		ns	10
34	t _{WL1GL2}	t _{WOH}	Write to $\overline{OE}$ Hold Time	10		13		15		ns	10
35	t _{CH2RH2}	t _{PRWC}	EDO Page Mode Read-Write Cycle Time	58		68		77		ns	
36	t _{RL2RL2} (RMW)	t _{RWC}	Read-Modify-Write Cycle Time	71		80		95		ns	
38	t _{CL1WL2}	t _{CWD}	$\overline{CAS}$ to $\overline{WE}$ Delay	31		35		45		ns	10
39	t _{RL1WL2}	t _{RWD}	$\overline{RAS}$ to $\overline{WE}$ Delay in Read-Modify-Write Cycle	68		80		95		ns	10
40	t _{AVWL2}	t _{AWD}	Column Address to $\overline{WE}$ Delay	43		50		60		ns	10
41	t _{CL2CL2}	t _{PC}	EDO Page Mode Read or Write Cycle Time	35		40		45		ns	
42	t _{CH2CL2}	t _{CP}	$\overline{CAS}$ Precharge Time	10		10		10		ns	
43	t _{AVRH1}	t _{CAR}	Column Address to $\overline{RAS}$ Setup Time	25		30		35		ns	
44	t _{CH2QV}	t _{CAP}	Access Time from Column Precharge		27		32		37	ns	6
46	t _{CL1RL2}	t _{CSR}	$\overline{CAS}$ Setup Time $\overline{CAS}$ -before- $\overline{RAS}$ Refresh	10		10		10		ns	
47	t _{RH2CL2}	t _{RPC}	$\overline{RAS}$ to $\overline{CAS}$ Precharge Time	5		5		5		ns	
48	t _{RL1CH1}	t _{CHR}	$\overline{CAS}$ Hold Time $\overline{CAS}$ -before- $\overline{RAS}$ Refresh	10		10		10		ns	
50	t _{RH2CL2}	t _{RASP}	$\overline{RAS}$ Pulse Width	50	200K	60	200K	70	200K	ns	
51	t _{RH2CL2}	t _{RHCP}	$\overline{CAS}$ Precharge Time to $\overline{RAS}$ Delay	30		35		40		ns	
52	t _{RH2CL2}	t _{CPWD}	$\overline{CAS}$ Precharge Time to $\overline{WE}$	48		55		65		ns	
53	t _{RH2CL2}	t _{CPT}	$\overline{CAS}$ Precharge Time (CBR Counter Test)	35		40		40		ns	
54	t _{RH2CL2}	t _{WRP}	Write to $\overline{RAS}$ Precharge time (CRB Cycle)	10		10		10		ns	
55	t _{RH2CL2}	t _{WRH}	Write Hold time reference to $\overline{RAS}$ (CRB Cycle)	10		10		10		ns	
56	t _{RH2CL2}	t _{CDD}	$\overline{CAS}$ High to Data delay	13		15		20		ns	16
57	t _{RH2CL2}	t _{ODD}	$\overline{OE}$ High to Data delay	13		15		20		ns	16
58	t _T	t _T	Transition Time (Rise and Fall)	3	50	3	50	3	50	ns	
59		t _{REF}	Refresh Interval (1024 Cycles)		16		16		16	ms	
		t _{REF}	Refresh Interval (1024 Cycles) (L-version)		256		256		256	ms	

Self Refresh AC Characteristics

60		t _{RASS}	$\overline{RAS}$ Pulse Width During Self Refresh	100K		100K		100K		ns	17
61		t _{RPS}	$\overline{RAS}$ Precharge Time During Self Refresh	95		110		130		ns	17
62		t _{CHS}	$\overline{CAS}$ Hold Time Width During Self Refresh	50		50		50		ns	17

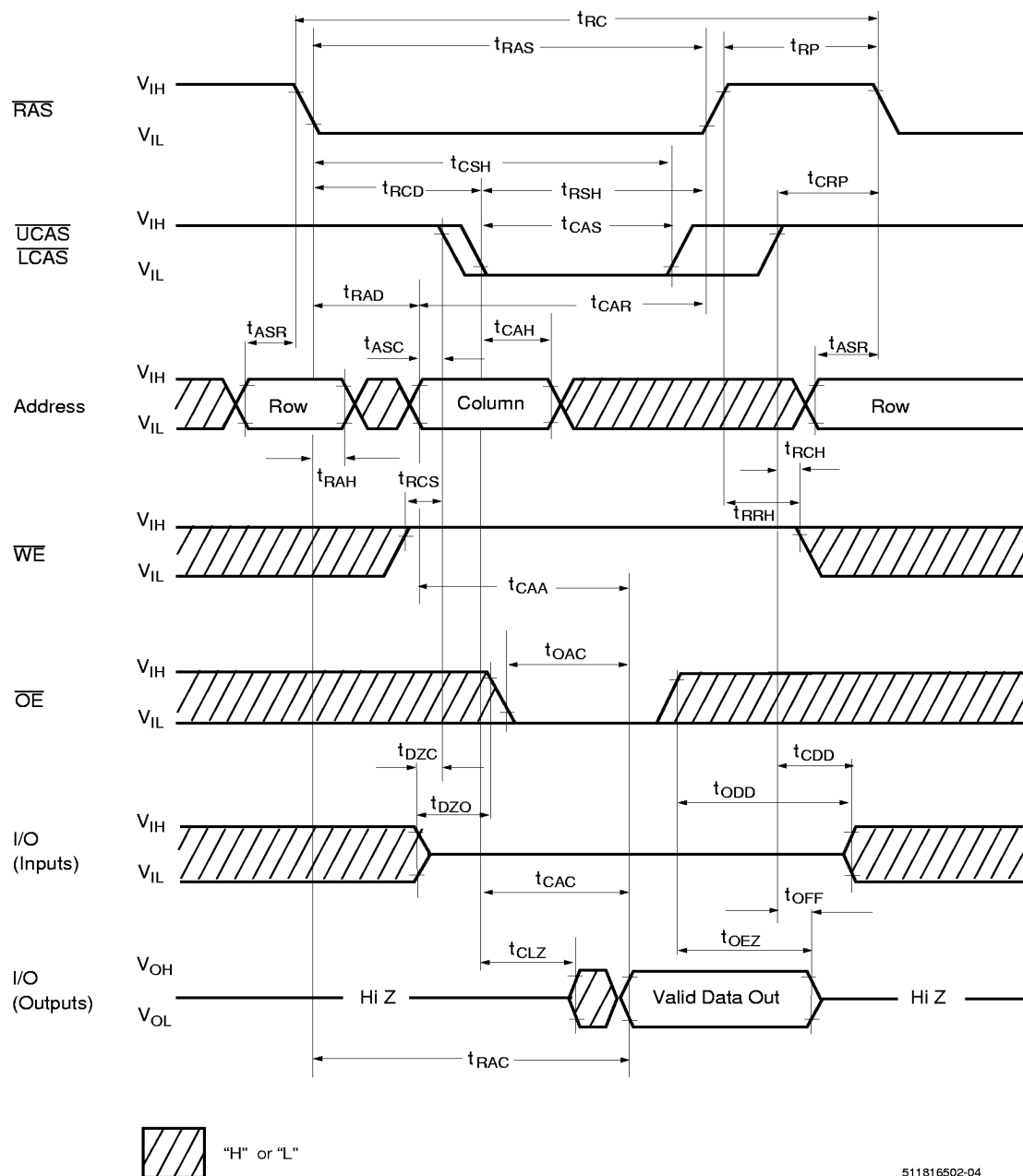
Notes:

1. All voltage are referenced to V_{SS} .
2. I_{CC1} , I_{CC3} , I_{CC4} , and I_{CC7} depend on cycle rate.
3. I_{CC1} and I_{CC4} depend on output loading. Specified values are measured with the output open.
4. Address can be changed once or less while $\overline{RAS} = V_{IL}$. In the case of I_{CC4} it can be changed once or less during an EDO cycle (t_{HPC}).
5. An initial pause of 200 μs is required after power-up followed by 8 $\overline{RAS}$ cycles of which at least one cycle has to be a refresh cycle, before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 $\overline{CAS}$ -before- $\overline{RAS}$ initialization cycles instead of 8 $\overline{RAS}$ cycles are required.
6. V_{IH} (min.) and V_{IL} (max.) are reference levels for measuring timing of input signals. Transition times are also measured between V_{IH} and V_{IL} .
7. Measured with a load equivalent to 2 TTL gates and 50 pF ($V_{OL} = 0.8V$ and $V_{OH} = 2.0V$).
8. t_{OFF} (max.) and t_{OEZ} (max.) define the time at which the outputs achieve the open-circuit condition and are not referenced to output voltage levels.
9. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
10. These parameters are referenced to the $\overline{CAS}$ leading edge in early write cycles and to the $\overline{WE}$ leading edge in read-write cycles.
11. t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} > t_{WCS}(\text{min.})$, the cycle is an early write cycle and the I/O pin will remain open-circuit (high impedance) through the entire cycle; if $t_{RWD} > t_{RWD}(\text{min.})$, $t_{CWD} > t_{CWD}(\text{min.})$, $t_{AWD} > t_{AWD}(\text{min.})$, and $t_{CPWD} > t_{CPWD}(\text{min.})$, the cycle is a read-write cycle and I/O pins will contain data read from the selected cells. If neither of the above sets of conditions is satisfied, the condition of the I/O pins (at access time) is indeterminate.
12. Operation within the $t_{RCD}(\text{max.})$ limit ensures that $t_{RAC}(\text{max.})$ can be met. $t_{RCD}(\text{max.})$ is specified as a reference point only: if t_{RCD} is greater than the specified $t_{RCD}(\text{max.})$ limit, then access time is controlled by t_{CAC} .
13. Operation within the $t_{RAD}(\text{max.})$ limit ensures that $t_{RAC}(\text{max.})$ can be met. $t_{RAD}(\text{max.})$ is specified as a reference point only: if t_{RAD} is greater than the specified $t_{RAD}(\text{max.})$ limit, then access time is controlled by t_{CAA} .
14. AC measurements assume $t_T = 2 \text{ ns}$.
15. Either t_{DZC} or t_{DEO} must be satisfied.
16. Either t_{CDD} or t_{ODD} must be satisfied.
17. When using Self Refresh mode, the following refresh operations must be performed to ensure proper DRAM operation:

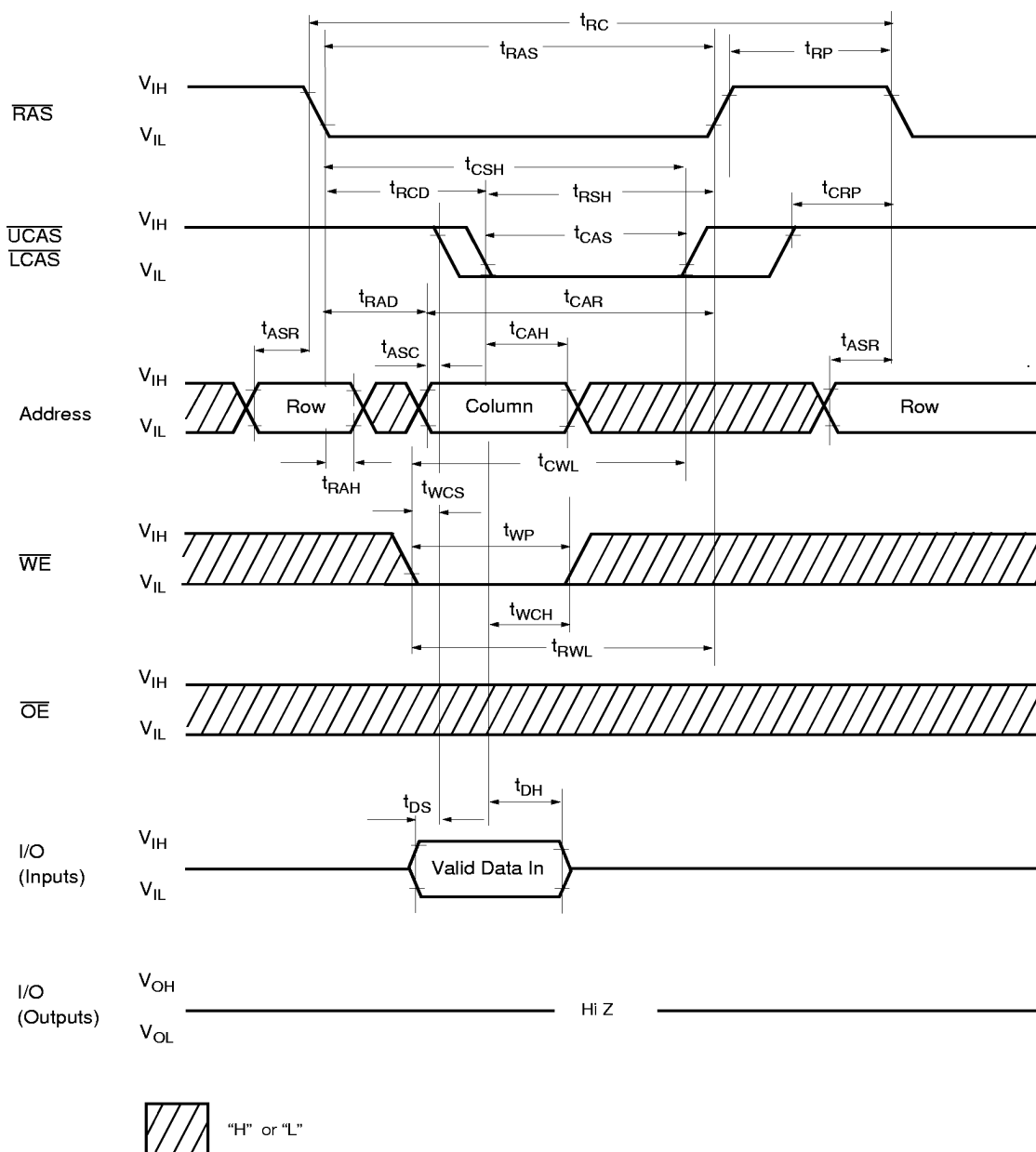
If row addresses are being refreshed on an evenly distributed manner over the refresh interval using CBR refresh cycles, then only one CBR cycle must be performed immediately after exit from Self Refresh.

If row addresses are being refreshed in any other manner (ROR – Distributed/Burst; or CBR – Burst) over the refresh interval, then a full set of row refreshes must be performed immediately before entry to and immediately after exit from Self Refresh.
18. t_{OFF} is referenced from the rising edge of $\overline{RAS}$ or $\overline{CAS}$, whichever occurs last.

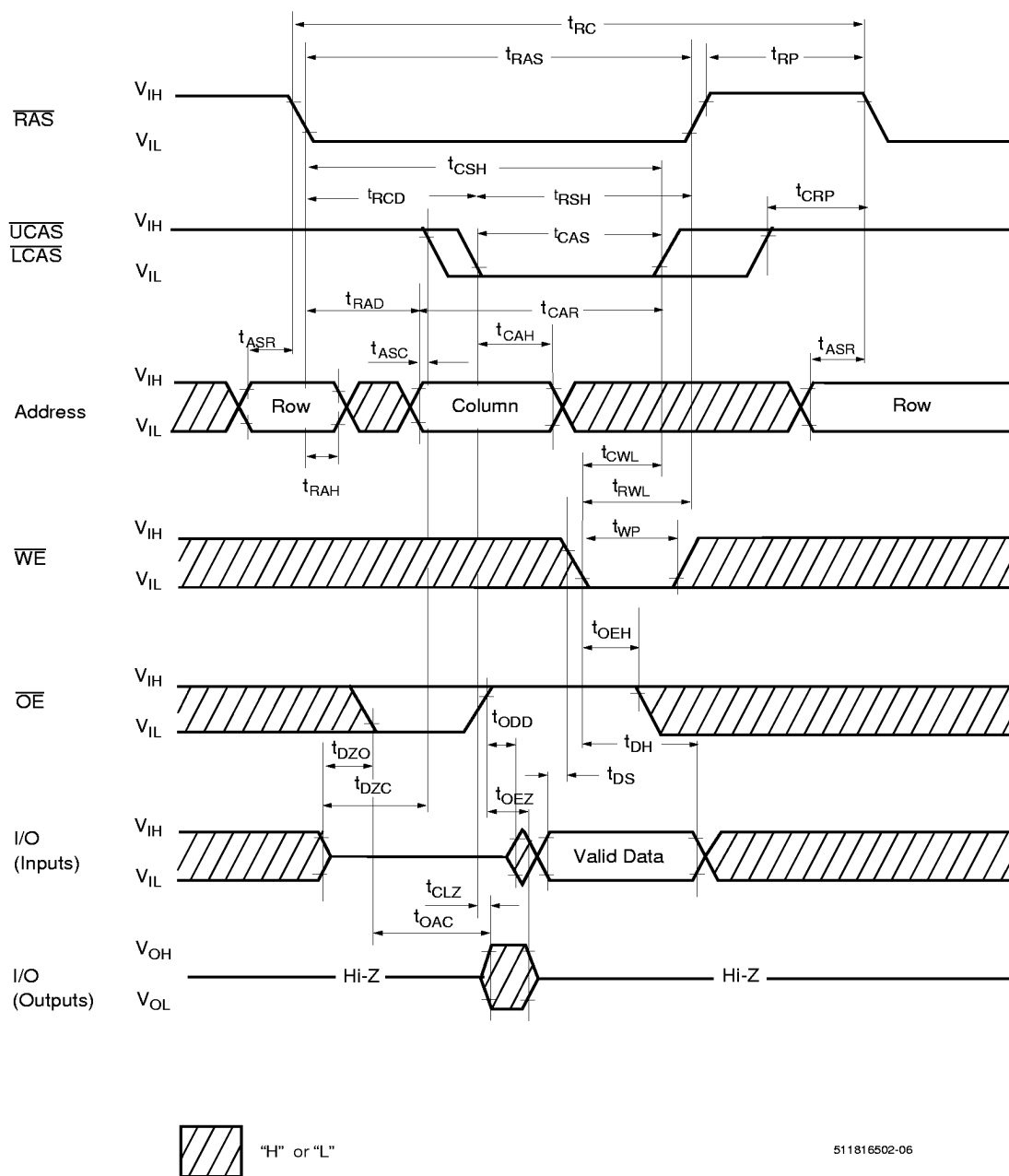
Waveforms of Read Cycle



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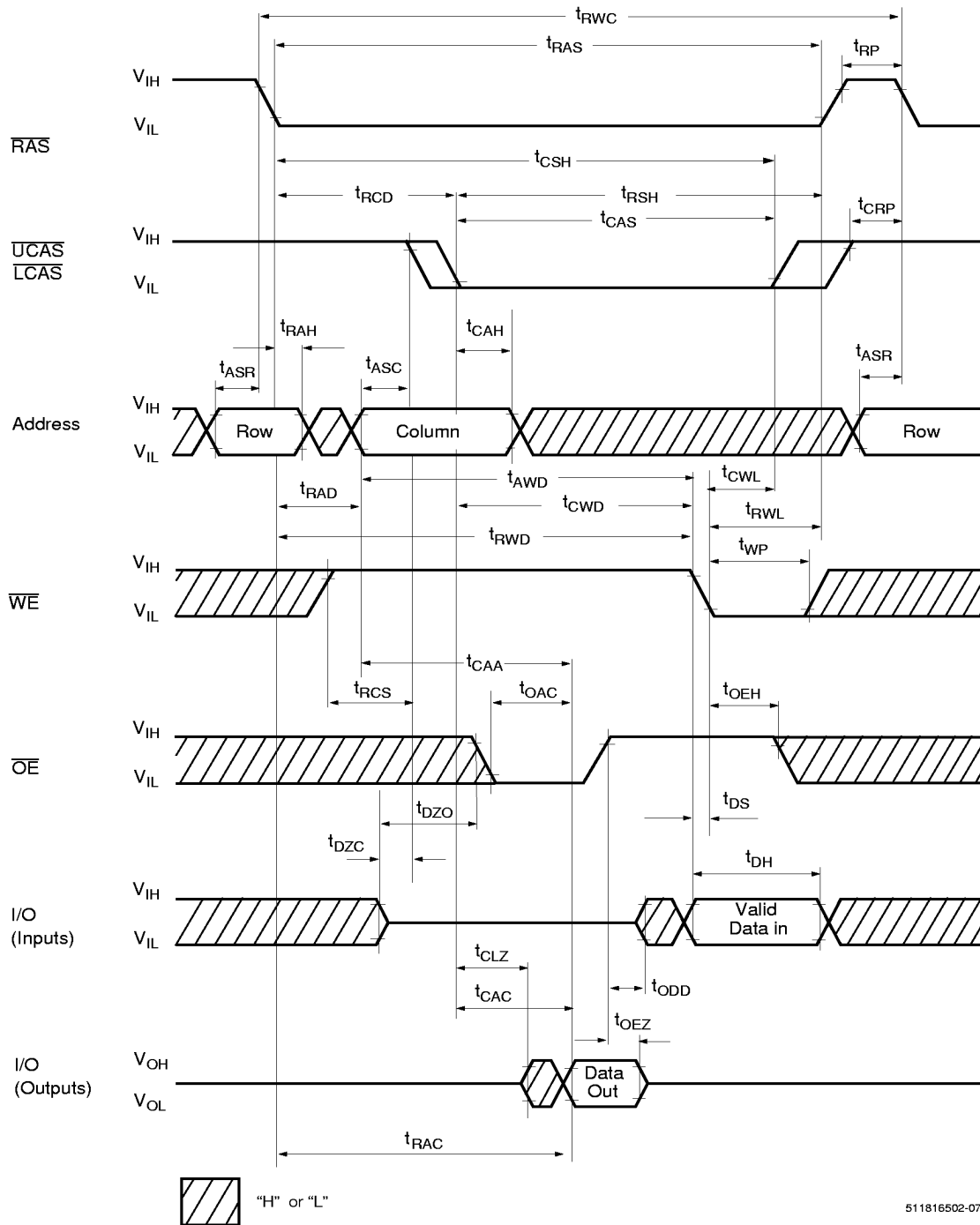
Waveforms of Write Cycle (Early Write)

511816502-05

Waveforms of Write Cycle ($\overline{OE}$ Controlled Write)

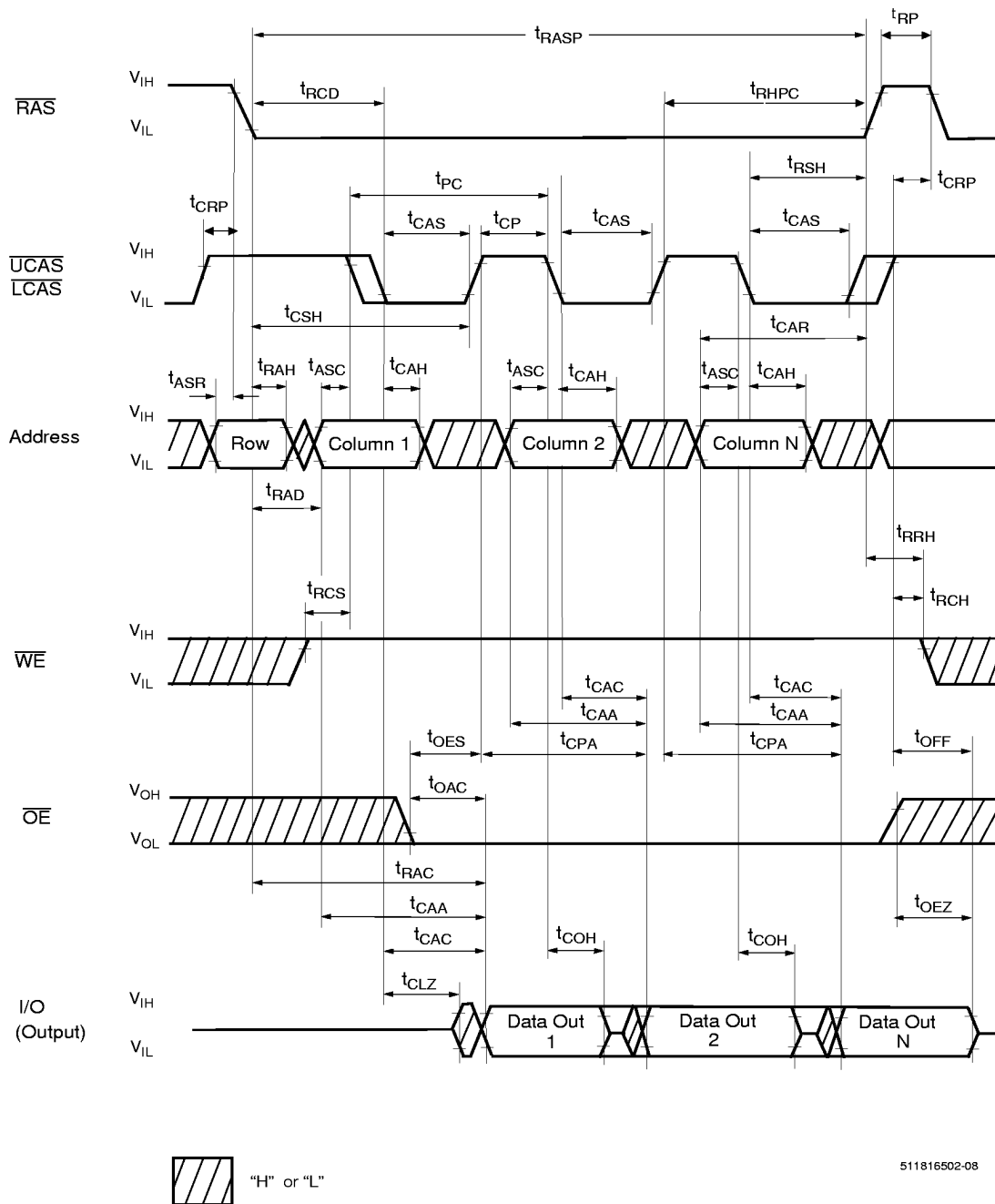
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Waveforms of Read-Write (Read-Modify-Write) Cycle



511816502-07

Waveforms of Fast Page Mode Read Cycle



511816502-08

Timing diagram for the 64K16V256 16-bit static CMOS RAM. The diagram illustrates the relationship between various control signals and data output over time.

Signals:

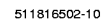
- $\overline{\text{RAS}}$: Row Address Strobe
- $\overline{\text{UCAS}}/\overline{\text{LCAS}}$: Column Address Strobe / Latch Enable
- Address**: Row and Column addresses
- $\overline{\text{WE}}$: Write Enable
- $\overline{\text{OE}}$: Output Enable
- I/O (Output)**: Data output signals (Data Out 1, Data Out 2, Data Out N)

Timing Parameters:

- t_{RASP} : RAS pulse width
- t_{RCD} : RAS to CAS delay
- t_{RHP} : RAS hold time
- t_{RP} : RAS recovery time
- t_{CRP} : CAS to RAS delay
- t_{PC} : Pulse width of CAS
- t_{CAS} : CAS pulse width
- t_{CP} : CAS to RAS delay
- t_{RSH} : RAS to CAS delay
- t_{CAR} : CAS to RAS delay
- t_{ASC} : Address to CAS delay
- t_{CAH} : Address to CAS hold time
- t_{ASR} : Address to RAS delay
- t_{RAH} : RAS to Address delay
- t_{ASC} : Address to CAS delay
- t_{CAH} : Address to CAS hold time
- t_{RAD} : RAS to Address delay
- t_{RCS} : RAS to CAS delay
- t_{CAC} : CAS to Address delay
- t_{CAA} : CAS to Address delay
- t_{CPA} : CAS to Address delay
- t_{OES} : Output Enable to Address delay
- t_{OEHC} : Output Enable to Address delay
- t_{OAC} : Output Enable to Address delay
- t_{OEP} : Output Enable to Address delay
- t_{OEZ} : Output Enable to Address delay
- t_{CLZ} : Output Enable to Address delay
- t_{RRH} : RAS to Address delay
- t_{RCH} : RAS to Address delay

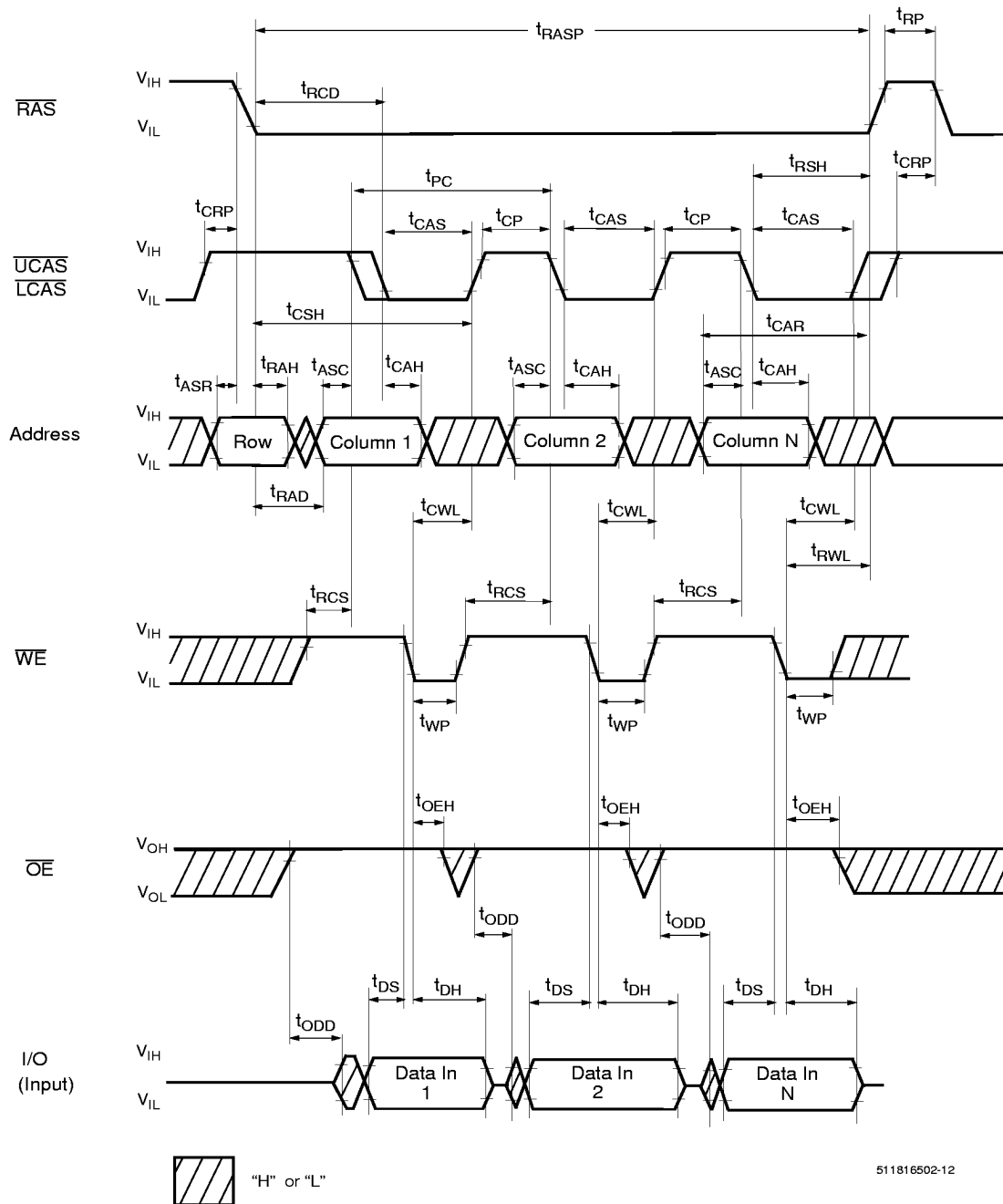
Legend: Hatched area indicates "H" or "L" level.

Waveforms of Fast Page Mode Read Cycle ($\overline{WE}$ Control)



[illegible]

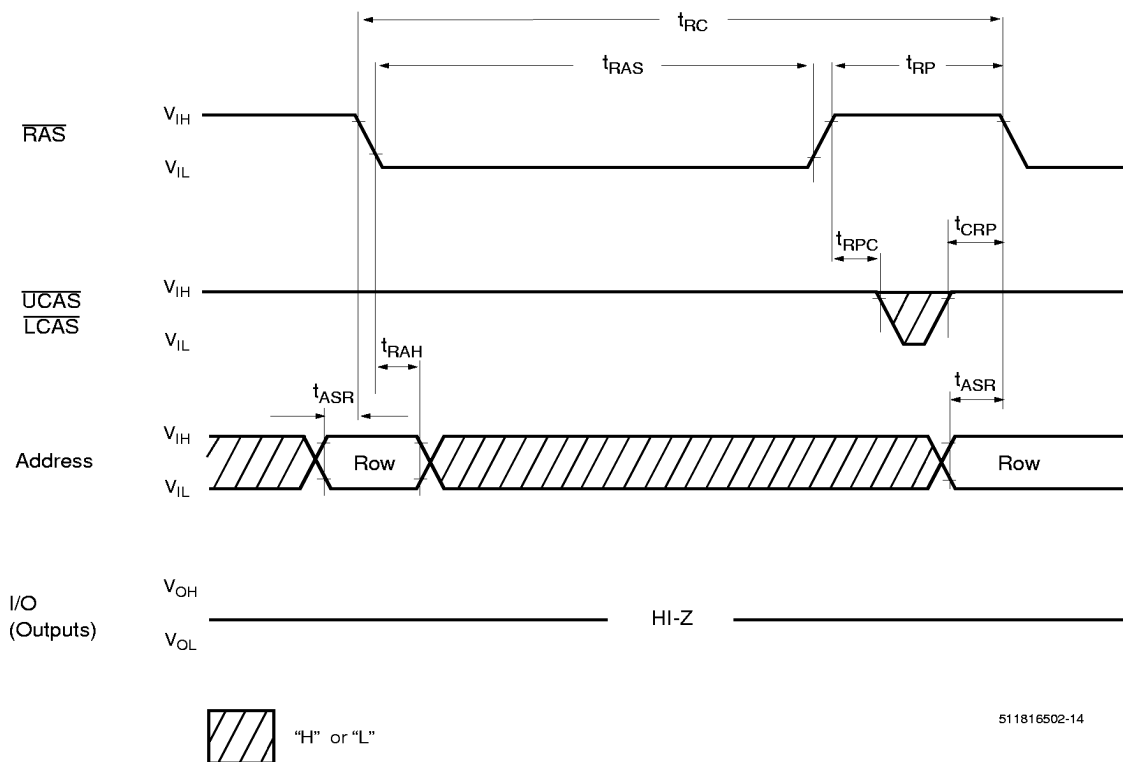
Waveforms of Fast Page Mode Late Write Cycle

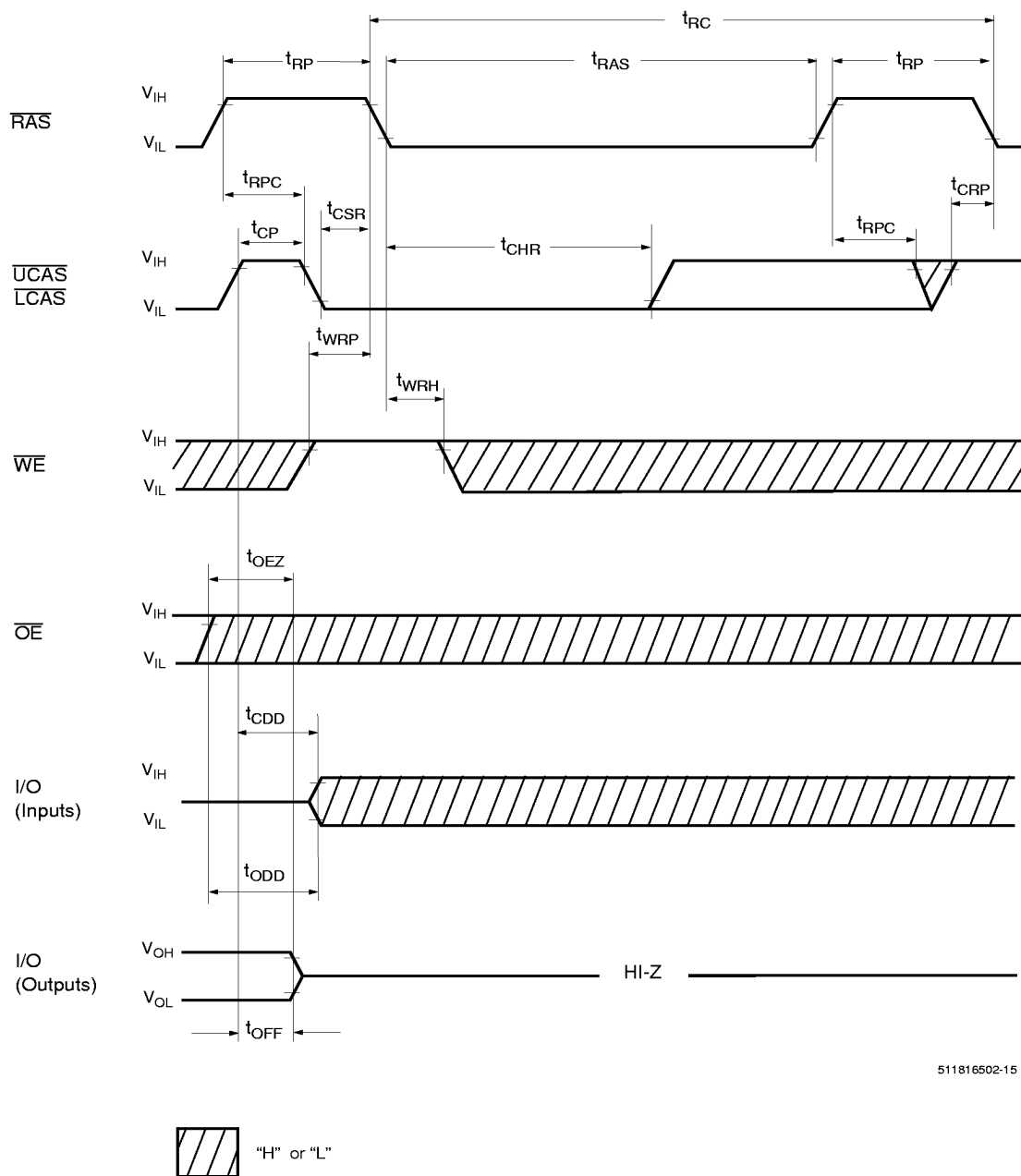


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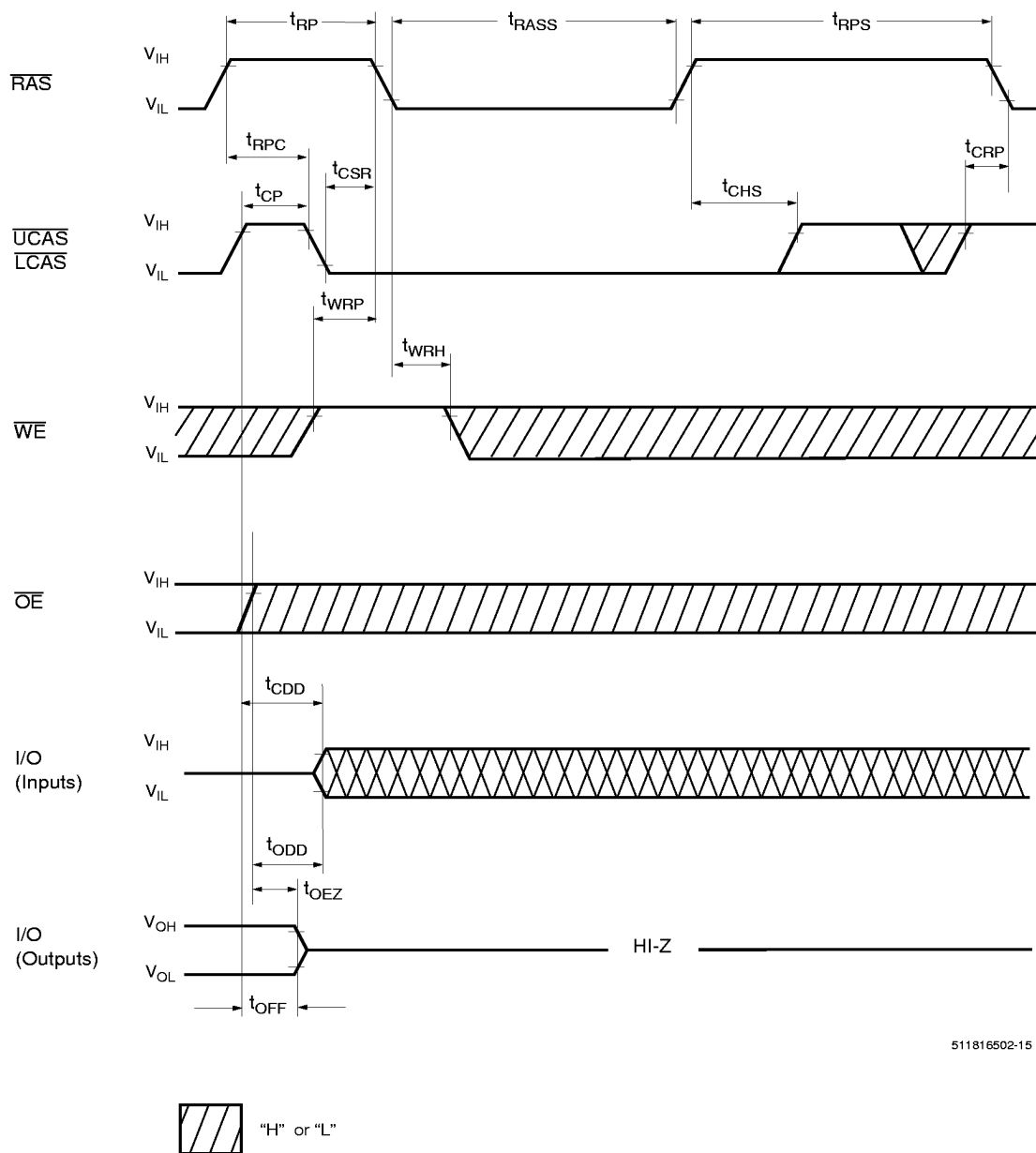
511816502-13



Waveforms of $\overline{\text{RAS}}$ Only Refresh Cycle

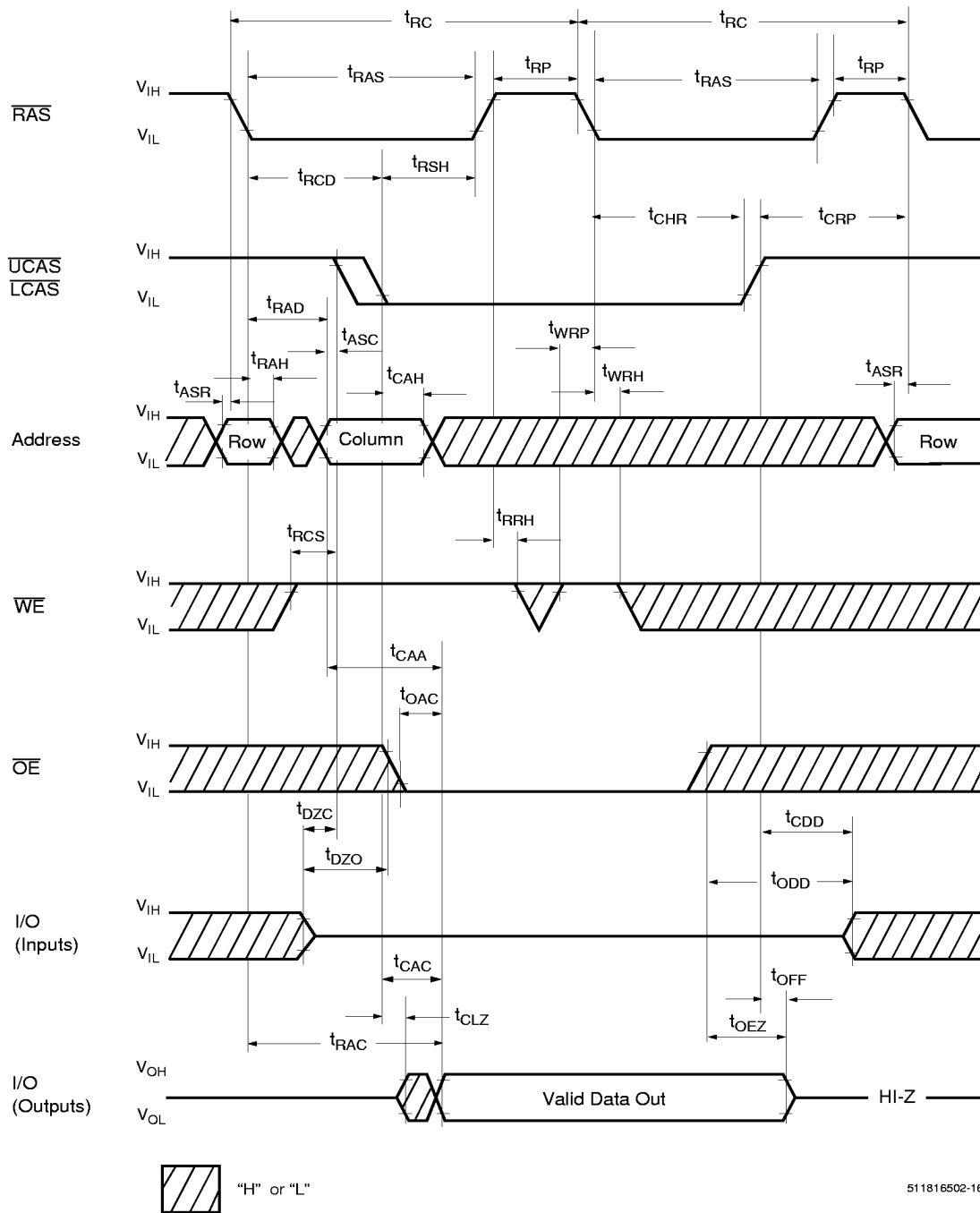
Waveforms of $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Refresh Cycle

511816502-15

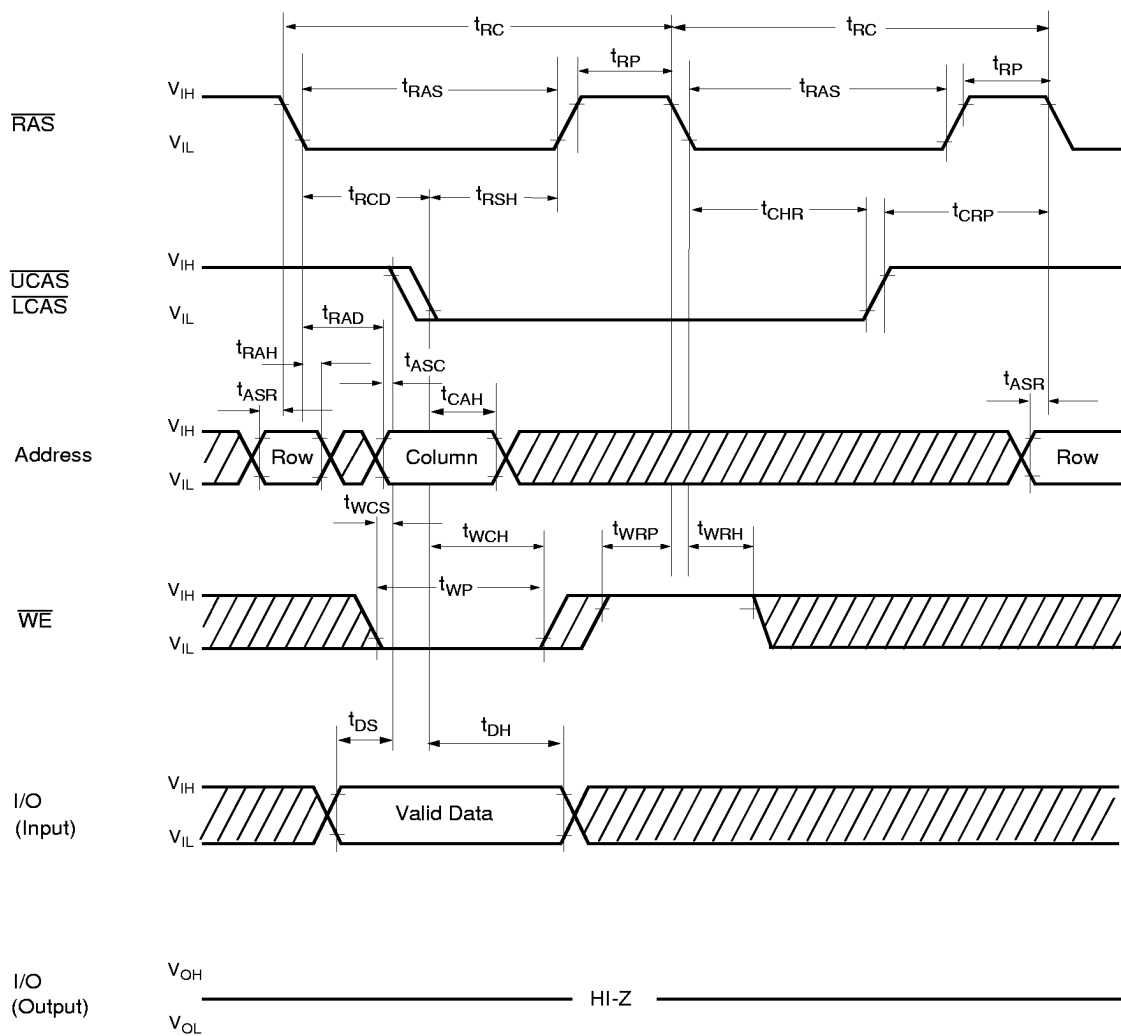
Waveforms of $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Self Refresh Cycle (Optional)

511816502-15

Waveforms of Hidden Refresh Read Cycle



511816502-16

Waveforms of Hidden Refresh Early Write Cycle

511816502-17

Functional Description

The V53C318160A is a CMOS dynamic RAM optimized for high data bandwidth, low power applications. It is functionally similar to a traditional dynamic RAM. The V53C318160A reads and writes data by multiplexing an 20-bit address into a 10-bit row and a 10-bit column address. The row address is latched by the Row Address Strobe ($\overline{\text{RAS}}$). The column address "flows through" an internal address buffer and is latched by the Column Address Strobe ($\overline{\text{CAS}}$). Because access time is primarily dependent on a valid column address rather than the precise time that the $\overline{\text{CAS}}$ edge occurs, the delay time from $\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ has little effect on the access time.

Memory Cycle

A memory cycle is initiated by bringing $\overline{\text{RAS}}$ low. Any memory cycle, once initiated, must not be ended or aborted before the minimum t_{RAS} time has expired. This ensures proper device operation and data integrity. A new cycle must not be initiated until the minimum precharge time $t_{\text{RP}}/t_{\text{CP}}$ has elapsed.

Read Cycle

A Read cycle is performed by holding the Write Enable ($\overline{\text{WE}}$) signal High during a $\overline{\text{RAS}}/\overline{\text{CAS}}$ operation. The column address must be held for a minimum specified by t_{AR} . Data Out becomes valid only when t_{OAC} , t_{RAC} , t_{CAA} and t_{CAC} are all satisfied. As a result, the access time is dependent on the timing relationships between these parameters. For example, the access time is limited by t_{CAA} when t_{RAC} , t_{CAC} and t_{OAC} are all satisfied.

Write Cycle

A Write Cycle is performed by taking $\overline{\text{WE}}$ and $\overline{\text{CAS}}$ low during a $\overline{\text{RAS}}$ operation. The column address is latched by $\overline{\text{CAS}}$. The Write Cycle can be $\overline{\text{WE}}$ controlled or $\overline{\text{CAS}}$ controlled depending on whether $\overline{\text{WE}}$ or $\overline{\text{CAS}}$ falls later. Consequently, the input data must be valid at or before the falling edge of $\overline{\text{WE}}$ or $\overline{\text{CAS}}$, whichever occurs last. In the $\overline{\text{CAS}}$ -controlled Write Cycle, when the leading edge of $\overline{\text{WE}}$ occurs prior to the $\overline{\text{CAS}}$ low transition, the I/O data pins will be in the High-Z state at the beginning of the Write function. Ending the Write with $\overline{\text{RAS}}$ or $\overline{\text{CAS}}$ will maintain the output in the High-Z state.

In the $\overline{\text{WE}}$ controlled Write Cycle, $\overline{\text{OE}}$ must be in the high state and t_{OED} must be satisfied.

Fast Page Mode

Fast Page operation permits all 1024 columns within a selected row of the device to be randomly

accessed at a high data rate. Maintaining $\overline{\text{RAS}}$ low while performing successive $\overline{\text{CAS}}$ cycles retains the row address internally and eliminates the need to reapply it for each cycle. The column address buffer acts as a transparent or flow-through latch while $\overline{\text{CAS}}$ is high. Thus, access begins from the occurrence of a valid column address rather than from the falling edge of $\overline{\text{CAS}}$, eliminating t_{ASC} and t_{T} from the critical timing path. $\overline{\text{CAS}}$ latches the address into the column address buffer. During Fast Page operation, Read, Write, Read-Modify-Write or Read-Write-Read cycles are possible at random addresses within a row. Following the initial entry cycle into EDO Mode, access is t_{CAA} or t_{CAP} controlled. If the column address is valid prior to the rising edge of $\overline{\text{CAS}}$, the access time is referenced to the $\overline{\text{CAS}}$ rising edge and is specified by t_{CAP} . If the column address is valid after the rising $\overline{\text{CAS}}$ edge, access is timed from the occurrence of a valid address and is specified by t_{CAA} . In both cases, the falling edge of $\overline{\text{CAS}}$ latches the address and enables the output.

Fast Page provides a sustained data rate of 29 MHz for applications that require high bandwidth such as bit-mapped graphics or high-speed signal processing. The following equation can be used to calculate the maximum data rate:

$$\text{Data Rate} = \frac{1024}{t_{\text{RC}} + 1023 \times t_{\text{PC}}}$$

Self Refresh

Self Refresh mode provides internal refresh control signals to the DRAM during extended periods of inactivity. Device operation in this mode provides additional power savings and design ease by elimination of external refresh control signals. Self Refresh mode is initiated with a $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ (CBR) Refresh cycle, holding both $\overline{\text{RAS}}$ low (t_{RASS}) and $\overline{\text{CAS}}$ low (t_{CHD}) for a specified period. Both of these parameters are specified with minimum values to guarantee entry into Self Refresh operation. Once the device has been placed in to Self Refresh mode the $\overline{\text{CAS}}$ clock is no longer required to maintain Self Refresh operation.

The Self Refresh mode is terminated by returning the $\overline{\text{RAS}}$ clock to a high level for a specified (t_{RPS}) minimum time. After termination of the Self Refresh cycle normal accesses to the device may be initiated immediately, providing that subsequent refresh cycles utilize the $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ (CBR) mode of operation.

Data Output Operation

The V53C318160A Input/Output is controlled by $\overline{OE}$, $\overline{CAS}$, $\overline{WE}$ and $\overline{RAS}$. A $\overline{RAS}$ low transition enables the transfer of data to and from the selected row address in the Memory Array. A $\overline{RAS}$ high transition disables data transfer and latches the output data if the output is enabled. After a memory cycle is initiated with a $\overline{RAS}$ low transition, a $\overline{CAS}$ low transition or $\overline{CAS}$ low level enables the internal I/O path. A $\overline{CAS}$ high transition or a $\overline{CAS}$ high level disables the I/O path and the output driver if it is enabled. A $\overline{CAS}$ low transition while $\overline{RAS}$ is high has no effect on the I/O data path or on the output drivers. The output drivers, when otherwise enabled, can be disabled by holding $\overline{OE}$ high. The $\overline{OE}$ signal has no effect on any data stored in the output latches. A $\overline{WE}$ low level can also disable the output drivers when $\overline{CAS}$ is low. During a Write cycle, if $\overline{WE}$ goes low at a time in relationship to $\overline{CAS}$ that would normally cause the outputs to be active, it is necessary to use $\overline{OE}$ to disable the output drivers prior to the $\overline{WE}$ low transition to allow Data In Setup Time (t_{DS}) to be satisfied.

Power-On

After application of the V_{CC} supply, an initial pause of 200 μs is required followed by a minimum of 8 initialization cycles (any combination of cycles containing a $\overline{RAS}$ clock). Eight initialization cycles are required after extended periods of bias without clocks (greater than the Refresh Interval).

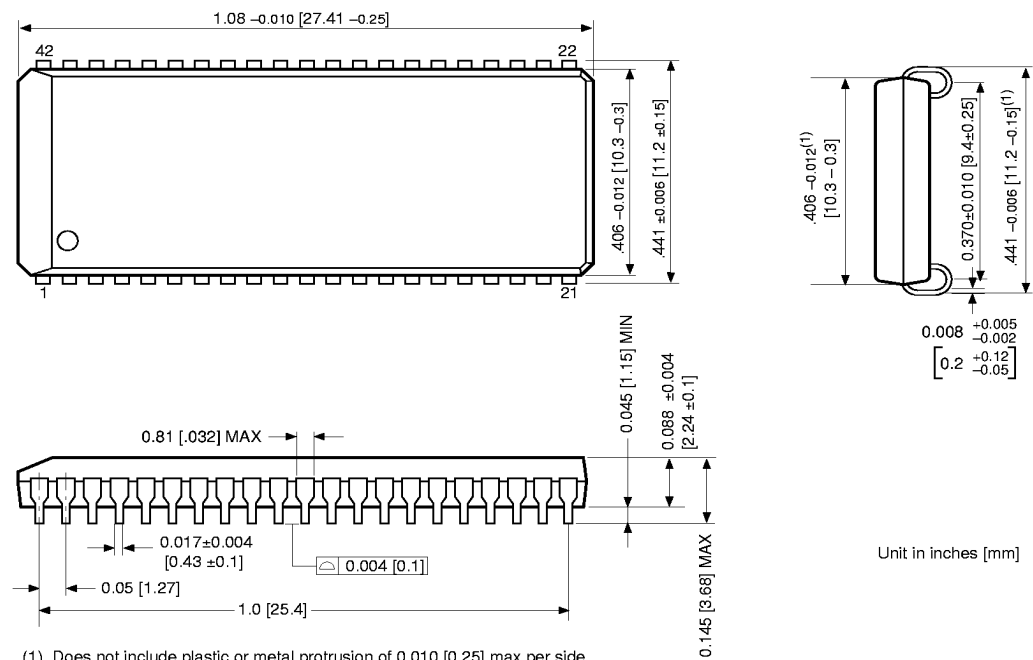
During Power-On, the V_{CC} current requirement of the V53C318160A is dependent on the input levels of $\overline{RAS}$ and $\overline{CAS}$. If $\overline{RAS}$ is low during Power-On, the device will go into an active cycle and I_{CC} will exhibit current transients. It is recommended that $\overline{RAS}$ and $\overline{CAS}$ track with V_{CC} or be held at a valid V_{IH} during Power-On to avoid current surges.

Table 1. V53C318160A Data Output Operation for Various Cycle Types

Cycle Type	I/O State
Read Cycles	Data from Addressed Memory Cell
CAS-Controlled Write Cycle (Early Write)	High-Z
$\overline{WE}$ -Controlled Write Cycle (Late Write)	$\overline{OE}$ Controlled. High $\overline{OE}$ = High-Z I/Os
Read-Modify-Write Cycles	Data from Addressed Memory Cell
EDO Read Cycle	Data from Addressed Memory Cell
EDO Write Cycle (Early Write)	High-Z
EDO Read-Modify-Write Cycle	Data from Addressed Memory Cell
$\overline{RAS}$ -only Refresh	High-Z
$\overline{CAS}$ -before- $\overline{RAS}$ Refresh Cycle	High-Z
$\overline{CAS}$ -only Cycles	High-Z

Package Diagrams

42-Pin 400 mil SOJ



50/44-Pin 400 mil TSOP-II

